

High frequency rectifier schottky barrier diode

RB491D

New

● Applications

Low power rectification

For switching power supply

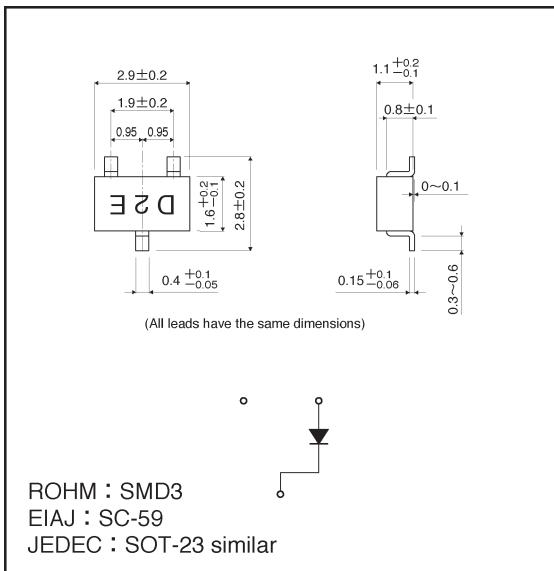
● Features

- 1) Small surface mounting type. (SMD3 (SC-59))
- 2) Extreme low forward voltage.
(typical capability of 0.45V at 1A)
- 3) $I_F = 1.0\text{A}$ achieved despite the size.

● Construction

Silicon epitaxial

● External dimensions (Units: mm)



● Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	25	V
DC reverse voltage	V_R	20	V
DC forward current	I_F	1.0	A
Peak forward surge current *	I_{FSM}	3	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40~+125	$^\circ\text{C}$

* 60 Hz for 1 mA

● Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	0.40	0.45	V	$I_F=1.0\text{A}$
Reverse current	I_R	—	—	200	μA	$V_R=20\text{V}$

* ESD sensitive product handling required.

- Electrical characteristic curves ($T_a = 25^\circ\text{C}$ unless specified otherwise)

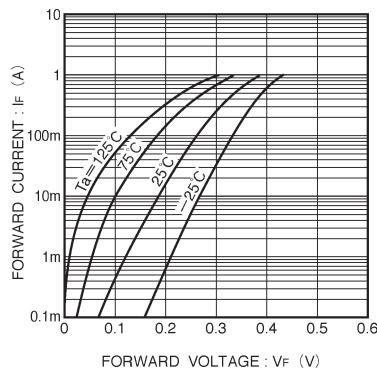


Fig. 1 Forward characteristics

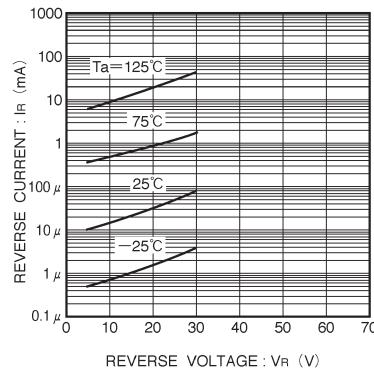


Fig. 2 Reverse characteristics

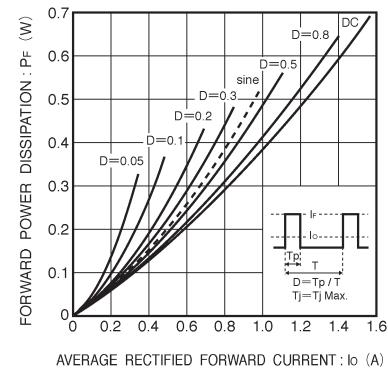
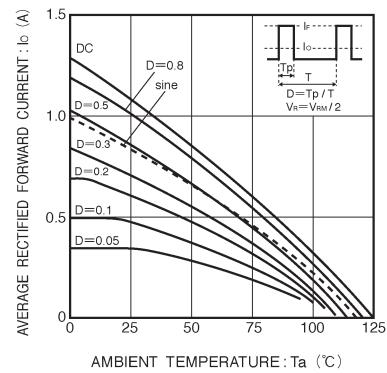


Fig. 3 Forward power dissipation characteristics

Fig. 4 Derating curve (I_o - T_a)